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Development of Ferroelectric Crystal Materials Measurement of Ferroelectric Properties for Relaxor Kazuhiko FUJITA

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Research Fields Electronic Materials, Instrument Technology

Keywords

Relaxor ferroelectrics, Piezoelectrics, permittivity

Research Outline

Crystal Growth of Relaxor typed Ferroelectrics

The ferroelectric materials are widely used as a key material of the electronic devices like a piezoelectric device, an ultrasonic transducer, or a FeRAM (ferroelectric random access memory), etc.. Relaxor typed ferroelectric crystals like (1-x)Pb(Zn1/3Nb2/3)O3xPbTiO₃ (abbr. (1-x)PZN-xPT) are grown with PbO flux by the flux method in electric furnace. The photograph below shows 0.95PZN-0.05PT single crystals grown in this method.





PZN-0.05PT

0.95PZN-0.05PT single crystals





Magnetron Sputter

Measurement of the Ferroelectric properties and Piezoelectric properties for the ferroelectric materials

(1-x)PZN-xPT crystals are polished using lapping shaped to the thin plate. After that, the paper, electrodes are sputtered on the both sides of (1-x)PZNxPT plate. The (1-x)PZN-xPT sample are formed into the capacitor. Using an impedance analyzer (HP4194A) and thermostatic furnace, the temperature dependence of the permittivity of the (1-x)PZN-xPT material is measured. The temperature dependence of the permittivity for 0.93PZN-0.07PT crystal in cooling process is shown in the following figure.



1.60E+04 500Hz 1kHz 0.93PZN-0.07P ά 1.40E+04 2kHz 5kHz Relative permittivity 1.20E+04 10kHz 20kHz 1.00E+04 50kHz 100kHz 8.00E+03 200kHz 500kHz 6.00E+03 1000kHz 4.00E+03 2.00E+03 0.00E+00 100 150 0 50 200 250 300 350 400 Temperature [°C]

Temperature dependence of permittivity for 0.93 PZN-0.07PT

Impedance Analyzer